

AMENDMENTS TO THE CLAIMS:

Please cancel claims 12, 14-18, and 26-29, without prejudice or disclaimer of their subject matter, amend claims 19, 20, and 23, and add new claims 30-42, as indicated below. This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1.-18. (Canceled)

19. (Currently Amended) A semiconductor device, comprising:

a wiring disposed in a predetermined pattern above a substrate and mainly comprising a first metal element;

a protecting conductive layer disposed on a pad section of the wiring and mainly comprising a second metal element different from the first metal element; and

a barrier film, disposed between the wiring and the protecting conductive layer, that is formed by stacking two pairs or more of a layer made of a predetermined metal element and a layer made of a compound mainly comprising the predetermined metal element.

20. (Currently Amended) The semiconductor device according to claim 19, wherein each of the layers forming the barrier film has ~~each layer configuring the pair, the each layer being formed in~~ a thickness of 5 nm or more to 30 nm or less.

21. (Original) The semiconductor device according to claim 19, wherein the barrier film is formed by stacking six pairs or less.

22. (Original) The semiconductor device according to claim 19, wherein the barrier film is formed of the same pairs only.

23. (Currently Amended) The semiconductor device according to claim 19, wherein the predetermined metal element is selected from Group IVa, Group Va or Group VIa.

24. (Original) The semiconductor device according to claim 23, wherein the compound is nitride.

25. (Original) The semiconductor device according to claim 24, wherein the wiring is formed of Cu, the protecting conductive layer is formed of Al, and the barrier film is formed of the pairs of Ta and Ta₂N.

26.-29. (Canceled)

30. (New) A semiconductor device, comprising:
a wiring including a pad section, disposed in a predetermined pattern above a substrate;
an insulating film formed on the wiring and having an opening at a position corresponding to the pad section;
a protecting conductive layer disposed on the pad section of the wiring; and

a barrier film, disposed between the wiring and the protecting conductive layer and on a sidewall of the opening of the insulating film, that is formed by stacking two pairs or more of a layer made of a predetermined metal element and a layer made of a compound mainly comprising the predetermined metal element.

31. (New) The semiconductor device according to claim 30, wherein each of the layers forming the barrier film has a thickness of 5 nm or more to 30 nm or less.

32. (New) The semiconductor device according to claim 30, wherein the barrier film is formed by stacking six pairs or less.

33. (New) The semiconductor device according to claim 30, wherein the barrier film is formed of the same pairs only.

34. (New) The semiconductor device according to claim 30, wherein the predetermined metal element is selected from Group IVa, Group Va or Group VIa.

35. (New) The semiconductor device according to claim 34, wherein the compound is nitride.

36. (New) The semiconductor device according to claim 35, wherein the wiring is formed of Cu, the protecting conductive layer is formed of Al, and the barrier film is formed of the pairs of Ta and Ta₂N.

37. (New) The semiconductor device according to claim 30, wherein the wiring mainly comprises a first metal element and the protecting conductive layer mainly comprises a second metal element different from the first metal element.

38. (New) The semiconductor device according to claim 37, wherein each of the layers forming the barrier film has a thickness of 5 nm or more to 30 nm or less.

39. (New) The semiconductor device according to claim 37, wherein the barrier film is formed by stacking six pairs or less.

40. (New) The semiconductor device according to claim 37, wherein the barrier film is formed of the same pairs only.

41. (New) The semiconductor device according to claim 37, wherein the predetermined metal element is selected from Group IVa, Group Va or Group VIa.

42. (New) The semiconductor device according to claim 41, wherein the compound is nitride.